



Attorney Docket No. FUJ 99228 CIP
Client Matter. No. 80458.0004.001

Harrison

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Katsuyoshi MATSUURA, et al.

Serial No. 09/551,233

Filed: April 17, 2000

Title: SEMICONDUCTOR DEVICE HAVING A
FERROELECTRIC CAPACITOR AND A
FABRICATION PROCESS THEREOF

Examiner: H.-M. LEE

Art Unit: 2823

AMENDMENT & RESPONSE TO OFFICE ACTION

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated January 22, 2001 (Paper No. 5),
the period of response to which has been extended one month to May 22,
2001, by the attached Petition for Extension of Time and enclosed fee, please
amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claim 3 without prejudice or disclaimer.

Please amend claims 1 and 7 as follows:

1. (Amended) A method of fabricating a semiconductor device
having a ferroelectric capacitor, comprising the steps of:
forming an active device element on a substrate;
forming an insulation film over said substrate to cover said active
device element;
forming a lower electrode layer of said ferroelectric capacitor over said
insulation film;
forming a ferroelectric film on said lower electrode layer as a capacitor
insulation film of said ferroelectric capacitor;

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